

Andrew J Steckl

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ext. citations

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avg, IF

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L-index

#	Paper	IF	Citations
331	Superhydrophobic and oleophobic fibers by coaxial electrospinning. <i>Langmuir</i> , 2009 , 25, 9454-62	4	265
330	Enhanced emission efficiency in organic light-emitting diodes using deoxyribonucleic acid complex as an electron blocking layer. <i>Applied Physics Letters</i> , 2006 , 88, 171109	3.4	259
329	Red light emission by photoluminescence and electroluminescence from Eu-doped GaN. <i>Applied Physics Letters</i> , 1999 , 75, 1189-1191	3.4	245
328	Optoelectronic Properties and Applications of Rare-Earth-Doped GaN. <i>MRS Bulletin</i> , 1999 , 24, 33-38	3.2	242
327	A nearly ideal phosphor-converted white light-emitting diode. <i>Applied Physics Letters</i> , 2008 , 92, 143309	3.4	234
326	Rare-earth-doped GaN: growth, properties, and fabrication of electroluminescent devices. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2002 , 8, 749-766	3.8	233
325	Visible emission from Er-doped GaN grown by solid source molecular beam epitaxy. <i>Applied Physics Letters</i> , 1998 , 73, 1700-1702	3.4	193
324	Triaxial electrospun nanofiber membranes for controlled dual release of functional molecules. <i>ACS Applied Materials & Interfaces</i> , 2013 , 5, 8241-5	9.5	150
323	High-voltage Ni- and Pt-SiC Schottky diodes utilizing metal field plate termination. <i>IEEE Transactions on Electron Devices</i> , 1999 , 46, 456-464	2.9	150
322	Blue emission from Tm-doped GaN electroluminescent devices. <i>Applied Physics Letters</i> , 1999 , 75, 2184-2186	3.4	135
321	Photocatalytic Self Cleaning Textile Fibers by Coaxial Electrospinning. <i>ACS Applied Materials & Interfaces</i> , 2010 , 2, 2448-2455	9.5	123
320	Spectral and time-resolved photoluminescence studies of Eu-doped GaN. <i>Applied Physics Letters</i> , 2003 , 82, 1655-1657	3.4	121
319	Electrowetting on paper for electronic paper display. <i>ACS Applied Materials & Interfaces</i> , 2010 , 2, 3318-23	9.5	114
318	Red light emission by photoluminescence and electroluminescence from Pr-doped GaN on Si substrates. <i>Applied Physics Letters</i> , 1999 , 74, 2161-2163	3.4	114
317	Epitaxial growth of beta -SiC on Si by RTCVD with C/sub 3/H/sub 8/ and SiH/sub 4/. <i>IEEE Transactions on Electron Devices</i> , 1992 , 39, 64-74	2.9	114
316	A Review of SiC Reactive Ion Etching in Fluorinated Plasmas. <i>Physica Status Solidi (B): Basic Research</i> , 1997 , 202, 605-642	1.3	107
315	Nucleation and Void Formation Mechanisms in SiC Thin Film Growth on Si by Carbonization. <i>Journal of the Electrochemical Society</i> , 1995 , 142, 634-641	3.9	107

314	Refractory metal silicides: Thin-film properties and processing technology. <i>IEEE Transactions on Electron Devices</i> , 1983 , 30, 1480-1497	2.9	103
313	Aptamer-based lateral flow assay for point of care cortisol detection in sweat. <i>Sensors and Actuators B: Chemical</i> , 2019 , 283, 79-86	8.5	103
312	Three-color integration on rare-earth-doped GaN electroluminescent thin films. <i>Applied Physics Letters</i> , 2003 , 82, 502-504	3.4	101
311	Photoluminescence and lasing from deoxyribonucleic acid (DNA) thin films doped with sulforhodamine. <i>Applied Optics</i> , 2007 , 46, 1507-13	1.7	93
310	Coaxial Electrospinning Formation of Complex Polymer Fibers and their Applications. <i>ChemPlusChem</i> , 2019 , 84, 1453-1497	2.8	91
309	Long-term antimicrobial effect of nisin released from electrospun triaxial fiber membranes. <i>Acta Biomaterialia</i> , 2017 , 53, 242-249	10.8	89
308	Laser action in Eu-doped GaN thin-film cavity at room temperature. <i>Applied Physics Letters</i> , 2004 , 85, 4588-4590	3.4	89
307	Stress Biomarkers in Biological Fluids and Their Point-of-Use Detection. <i>ACS Sensors</i> , 2018 , 3, 2025-2044	9.2	89
306	Blood coagulation screening using a paper-based microfluidic lateral flow device. <i>Lab on A Chip</i> , 2014 , 14, 4035-41	7.2	88
305	Green electroluminescence from Er-doped GaN Schottky barrier diodes. <i>Applied Physics Letters</i> , 1998 , 73, 2450-2452	3.4	86
304	Three-color electrowetting display device for electronic paper. <i>Applied Physics Letters</i> , 2010 , 97, 023514	3.4	85
303	Multiple color capability from rare earth-doped gallium nitride. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2001 , 81, 97-101	3.1	81
302	Reactive ion etching of SiC thin films using fluorinated gases. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1986 , 4, 349		81
301	Prospects for rare earth doped GaN lasers on Si. <i>Materials Today</i> , 2007 , 10, 20-27	21.8	76
300	Visible and infrared rare-earth-activated electroluminescence from indium tin oxide Schottky diodes to GaN:Er on Si. <i>Applied Physics Letters</i> , 1999 , 74, 182-184	3.4	75
299	Structural characterization of nanometer SiC films grown on Si. <i>Applied Physics Letters</i> , 1993 , 62, 3135-3137	3.7	74
298	Reactive Ion Etching of SiC Thin Films by Mixtures of Fluorinated Gases and Oxygen. <i>Journal of the Electrochemical Society</i> , 1990 , 137, 212-220	3.9	74
297	Photoluminescence studies of rare earth (Er, Eu, Tm) in situ doped GaN. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2003 , 105, 91-96	3.1	73

296	Paper Microfluidics for Point-of-Care Blood-Based Analysis and Diagnostics. <i>Analytical Chemistry</i> , 2019 , 91, 352-371	7.8	72
295	Voltage-controlled yellow or orange emission from GaN codoped with Er and Eu. <i>Applied Physics Letters</i> , 2000 , 76, 1525-1527	3.4	70
294	Exploring the Potential of Nucleic Acid Bases in Organic Light Emitting Diodes. <i>Advanced Materials</i> , 2015 , 27, 7552-62	24	69
293	Optical and magnetic properties of Eu-doped GaN. <i>Applied Physics Letters</i> , 2006 , 89, 132119	3.4	69
292	Growth of crystalline 3C-SiC on Si at reduced temperatures by chemical vapor deposition from silacyclobutane. <i>Applied Physics Letters</i> , 1993 , 63, 3347-3349	3.4	67
291	Heteroepitaxial Growth of SiC on Si(100) and (111) by Chemical Vapor Deposition Using Trimethylsilane. <i>Journal of the Electrochemical Society</i> , 1999 , 146, 1197-1202	3.9	64
290	Electrospun carbon nanofiber modified electrodes for stripping voltammetry. <i>Analytical Chemistry</i> , 2015 , 87, 9315-21	7.8	60
289	Nanofiber-Based Bulk-Heterojunction Organic Solar Cells Using Coaxial Electrospinning. <i>Advanced Energy Materials</i> , 2012 , 2, 1136-1144	21.8	60
288	SiC rapid thermal carbonization of the (111)Si semiconductor-on-insulator structure and subsequent metalorganic chemical vapor deposition of GaN. <i>Applied Physics Letters</i> , 1996 , 69, 2264-2266	3.4	60
287	Red emission from Eu-doped GaN luminescent films grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2003 , 83, 9-11	3.4	59
286	High speed nanofluidic protein accumulator. <i>Lab on A Chip</i> , 2009 , 9, 1890-6	7.2	58
285	A comparative study of electrode effects on the electrical and luminescent characteristics of Alq3/TPD OLED: Improvements due to conductive polymer (PEDOT) anode. <i>Journal of Luminescence</i> , 2007 , 126, 225-229	3.8	56
284	Improved Performance of OLEDs on Cellulose/Epoxy Substrate Using Adenine as a Hole Injection Layer. <i>ACS Photonics</i> , 2015 , 2, 439-445	6.3	55
283	High brightness phosphorescent organic light emitting diodes on transparent and flexible cellulose films. <i>Nanotechnology</i> , 2014 , 25, 094012	3.4	55
282	Maximizing Alq/sub 3/ OLED internal and external efficiencies: charge balanced device structure and color conversion outcoupling lenses. <i>Journal of Display Technology</i> , 2006 , 2, 143-152		55
281	Green emission from Er-doped GaN grown by molecular beam epitaxy on Si substrates. <i>Applied Physics Letters</i> , 1998 , 73, 2143-2145	3.4	55
280	Excitation pathways and efficiency of Eu ions in GaN by site-selective spectroscopy. <i>Applied Physics B: Lasers and Optics</i> , 2009 , 97, 607-618	1.9	53
279	High-transmission electrowetting light valves. <i>Applied Physics Letters</i> , 2005 , 86, 151121	3.4	53

278	Local structure and bonding of Er in GaN: A contrast with Er in Si. <i>Applied Physics Letters</i> , 2000 , 76, 2865-2867	3.4	52
277	The effect of ambient atmosphere in the annealing of indium tin oxide films. <i>Journal of Applied Physics</i> , 1980 , 51, 3890-3895	2.5	52
276	Temperature dependence of energy transfer mechanisms in Eu-doped GaN. <i>Journal of Applied Physics</i> , 2004 , 95, 7717-7724	2.5	51
275	Photoluminescence properties of in situ Tm-doped Al _x Ga _{1-x} N. <i>Applied Physics Letters</i> , 2003 , 83, 4556-4558	3.4	51
274	Residue-free reactive ion etching of SiC in CHF ₃ /O ₂ with H ₂ additive. <i>Applied Physics Letters</i> , 1992 , 60, 1966-1968	3.4	51
273	ELiXIR-Solid-State Luminaire With Enhanced Light Extraction by Internal Reflection. <i>Journal of Display Technology</i> , 2007 , 3, 155-159		50
272	. <i>IEEE Spectrum</i> , 2013 , 50, 48-61	1.7	47
271	Voltage control of droplet interface bilayer lipid membrane dimensions. <i>Langmuir</i> , 2011 , 27, 618-26	4	47
270	Enhanced blue emission from Tm-doped Al _x Ga _{1-x} N electroluminescent thin films. <i>Applied Physics Letters</i> , 2003 , 83, 2094-2096	3.4	47
269	Spectroscopic and energy transfer studies of Eu ³⁺ centers in GaN. <i>Journal of Applied Physics</i> , 2007 , 102, 073520	2.5	46
268	The trials of wafer-scale integration: Although major technical problems have been overcome since WSI was first tried in the 1960s, commercial companies can't yet make it fly. <i>IEEE Spectrum</i> , 1984 , 21, 32-39	1.7	45
267	Residue-Free Reactive Ion Etching of Silicon Carbide in Fluorinated Plasmas: II .. <i>Journal of the Electrochemical Society</i> , 1995 , 142, 312-319	3.9	44
266	Characterization of 3C-SiC crystals grown by thermal decomposition of methyltrichlorosilane. <i>Applied Physics Letters</i> , 1996 , 69, 3824-3826	3.4	43
265	Stimuli-Responsive Self-Immolative Polymer Nanofiber Membranes Formed by Coaxial Electrospinning. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 11858-11865	9.5	42
264	Pentacene organic thin-film transistors on flexible paper and glass substrates. <i>Nanotechnology</i> , 2014 , 25, 094005	3.4	41
263	Localized fabrication of Si nanostructures by focused ion beam implantation. <i>Applied Physics Letters</i> , 1992 , 60, 1833-1835	3.4	40
262	Enhanced blue and green emission in rare-earth-doped GaN electroluminescent devices by optical photopumping. <i>Applied Physics Letters</i> , 2002 , 81, 2331-2333	3.4	39
261	Effects of Hydrogen Additive on Obtaining Residue-Free Reactive Ion Etching of SiC in Fluorinated Plasmas. <i>Journal of the Electrochemical Society</i> , 1993 , 140, 1813-1824	3.9	39

260	Effect of carbonization on the growth of 3C-SiC on Si (111) by silacyclobutane. <i>Applied Physics Letters</i> , 1994 , 64, 3000-3002	3-4	39
259	Optimum Er concentration for in situ doped GaN visible and infrared luminescence. <i>Applied Physics Letters</i> , 2001 , 79, 719-721	3-4	38
258	Deactivating chemical agents using enzyme-coated nanofibers formed by electrospinning. <i>ACS Applied Materials & Interfaces</i> , 2011 , 3, 4633-9	9-5	37
257	Optically active centers in Eu implanted, Eu in situ doped GaN, and Eu doped GaN quantum dots. <i>Journal of Applied Physics</i> , 2009 , 105, 043104	2-5	37
256	Effect of optical excitation energy on the red luminescence of Eu ³⁺ in GaN. <i>Applied Physics Letters</i> , 2005 , 86, 051110	3-4	37
255	Focused ion beam micromilling of GaN and related substrate materials (sapphire, SiC, and Si). <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 362		37
254	Doping-induced selective area photoluminescence in porous silicon. <i>Applied Physics Letters</i> , 1993 , 62, 1982-1984	3-4	37
253	Selective pH-Responsive Core-Sheath Nanofiber Membranes for Chem/Bio/Med Applications: Targeted Delivery of Functional Molecules. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 42653-42660	9-5	35
252	Molecular beam deposition of DNA nanometer films. <i>Nano Letters</i> , 2007 , 7, 133-7	11-5	35
251	Heat conduction in silicon thin films: Effect of microstructure. <i>Journal of Materials Research</i> , 1995 , 10, 1889-1896	2-5	34
250	Thermal Oxidation of Sputtered Silicon Carbide Thin Films. <i>Journal of the Electrochemical Society</i> , 1984 , 131, 1907-1914	3-9	34
249	Effect of Si codoping on Eu ³⁺ luminescence in GaN. <i>Journal of Applied Physics</i> , 2009 , 105, 043107	2-5	33
248	Molecular beam epitaxy growth of SiC on Si(111) from silacyclobutane. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998 , 16, 1305		33
247	Photoluminescence from stain-etched polycrystalline Si thin films. <i>Applied Physics Letters</i> , 1993 , 62, 2111-2113	3-4	33
246	Application of charge-coupled devices to infrared detection and imaging. <i>Proceedings of the IEEE</i> , 1975 , 63, 67-74	14-3	33
245	Low-voltage GaN:Er green electroluminescent devices. <i>Applied Physics Letters</i> , 2000 , 76, 1365-1367	3-4	32
244	Room-temperature visible and infrared photoluminescence from Pr-implanted GaN films by focused-ion-beam direct write. <i>Applied Physics Letters</i> , 1999 , 74, 2364-2366	3-4	32
243	Intense switchable fluorescence in light wave coupled electrowetting devices. <i>Applied Physics Letters</i> , 2005 , 86, 011105	3-4	31

242	Silicon Carbide Wafer Bonding. <i>Journal of the Electrochemical Society</i> , 1995 , 142, 232-236	3.9	31
241	. <i>IEEE Transactions on Electron Devices</i> , 1994 , 41, 281-287	2.9	31
240	DNA bases thymine and adenine in bio-organic light emitting diodes. <i>Scientific Reports</i> , 2014 , 4, 7105	4.9	30
239	Lateral color integration on rare-earth-doped GaN electroluminescent thin films. <i>Applied Physics Letters</i> , 2002 , 80, 1888-1890	3.4	30
238	Microbial Power-Generating Capabilities on Micro-/Nano-Structured Anodes in Micro-Sized Microbial Fuel Cells. <i>Fuel Cells</i> , 2014 , 14, 801-809	2.9	29
237	Triggered release of molecules across droplet interface bilayer lipid membranes using photopolymerizable lipids. <i>Langmuir</i> , 2012 , 28, 7657-64	4	29
236	Enhanced Performance of Micro-Electro-Mechanical-Systems (MEMS) Microbial Fuel Cells Using Electrospun Microfibrous Anode and Optimizing Operation. <i>Fuel Cells</i> , 2013 , 13, 336-341	2.9	29
235	Role of surfactants in the interaction of dye molecules in natural DNA polymers. <i>Langmuir</i> , 2009 , 25, 11698-702	4	29
234	Label-Free Optical Detection of Multiple Biomarkers in Sweat, Plasma, Urine, and Saliva. <i>ACS Sensors</i> , 2019 , 4, 1346-1357	9.2	28
233	Lateral flow assay using aptamer-based sensing for on-site detection of dopamine in urine. <i>Analytical Biochemistry</i> , 2020 , 596, 113637	3.1	28
232	Integrated OLED as excitation light source in fluorescent lateral flow immunoassays. <i>Biosensors and Bioelectronics</i> , 2015 , 74, 150-5	11.8	27
231	Temperature behavior of visible and infrared electroluminescent devices fabricated on erbium-doped GaN. <i>IEEE Transactions on Electron Devices</i> , 2002 , 49, 48-54	2.9	27
230	Photonic Applications of Rare-Earth-Doped Materials. <i>MRS Bulletin</i> , 1999 , 24, 16-20	3.2	27
229	Residue-Free Reactive Ion Etching of 3 C - SiC and 6 H - SiC in Fluorinated Mixture Plasmas. <i>Journal of the Electrochemical Society</i> , 1995 , 142, 2853-2860	3.9	27
228	Thermal oxidation of niobium silicide thin films. <i>Journal of Applied Physics</i> , 1983 , 54, 2716-2719	2.5	27
227	Point-of-care coagulation monitoring: first clinical experience using a paper-based lateral flow diagnostic device. <i>Biomedical Microdevices</i> , 2017 , 19, 64	3.7	26
226	Damage generation and removal in the Ga ⁺ focused ion beam micromachining of GaN for photonic applications. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 3063		26
225	Shallow Si p+n junctions fabricated by focused ion beam Ga ⁺ implantation through thin Ti and TiSi ₂ layers. <i>Journal of Applied Physics</i> , 1993 , 74, 2318-2322	2.5	26

224	Plasma Etching of Refractory Gates for VLSI Applications. <i>Journal of the Electrochemical Society</i> , 1984 , 131, 2325-2335	3.9	26
223	Plasma etching of sputtered Mo and MoSi ₂ thin films in NF ₃ gas mixtures. <i>Journal of Applied Physics</i> , 1982 , 53, 5531-5540	2.5	26
222	GaN focused ion beam micromachining with gas-assisted etching. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001 , 19, 2547		25
221	Photoluminescence studies and read/write process of a strong two-photon absorbing chromophore. <i>Applied Physics Letters</i> , 2000 , 77, 328-330	3.4	25
220	Aptamer-Based Lateral Flow Biosensor for Rapid Detection of Salivary Cortisol. <i>ACS Omega</i> , 2020 , 5, 32890-32898	3.9	25
219	Multi-layered core-sheath fiber membranes for controlled drug release in the local treatment of brain tumor. <i>Scientific Reports</i> , 2019 , 9, 17936	4.9	25
218	Correlation between compositional fluctuation and magnetic properties of Tm-doped AlGa _N alloys. <i>Applied Physics Letters</i> , 2007 , 91, 222503	3.4	23
217	Optical amplification and electroluminescence at 1.54 μ m in Er-doped zinc silicate germanate on silicon. <i>Applied Physics Letters</i> , 2004 , 84, 1462-1464	3.4	23
216	Spectroscopic studies of the visible and infrared luminescence from Er doped GaN. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2001 , 81, 116-120	3.1	23
215	Room-temperature-grown rare-earth-doped GaN luminescent thin films. <i>Applied Physics Letters</i> , 2001 , 79, 1962-1964	3.4	23
214	Si Oxyhydrides on Stain-Etched Porous Si Thin Films and Correlation with Crystallinity and Photoluminescence. <i>Journal of the Electrochemical Society</i> , 1995 , 142, L69-L71	3.9	23
213	Multilevel interconnections for wafer scale integration. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1986 , 4, 3127-3138	2.9	23
212	Effect of growth conditions on Eu ³⁺ luminescence in GaN. <i>Journal of Crystal Growth</i> , 2010 , 312, 680-684	1.6	22
211	SiC thin-film Fabry-Perot interferometer for fiber-optic temperature sensor. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 2159-2164	2.9	22
210	Ga flux dependence of Er-doped GaN luminescent thin films. <i>Applied Physics Letters</i> , 2002 , 80, 728-730	3.4	22
209	SiC Silicon-on-Insulator Structures by Direct Carbonization Conversion and Postgrowth from Silacyclobutane. <i>Journal of the Electrochemical Society</i> , 1994 , 141, L66-L68	3.9	22
208	Immunoassay on free-standing electrospun membranes. <i>ACS Applied Materials & Interfaces</i> , 2010 , 2, 252-8	9.5	21
207	Versatile Core-Sheath Biofibers using Coaxial Electrospinning. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1094, 1		21

206	RBS/Channeling study of Er doped GaN films grown by MBE on Si substrates. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2000 , 161-163, 946-951	1.2	21
205	Rapid thermal chemical vapor deposition growth of nanometer-thin SiC on silicon. <i>Thin Solid Films</i> , 1992 , 216, 149-154	2.2	21
204	Flow reproducibility of whole blood and other bodily fluids in simplified no reaction lateral flow assay devices. <i>Biomicrofluidics</i> , 2017 , 11, 024116	3.2	20
203	GaN:Eu electroluminescent devices grown by interrupted growth epitaxy. <i>Thin Solid Films</i> , 2006 , 496, 636-642	2.2	20
202	Review of focused ion beam implantation mixing for the fabrication of GaAs-based optoelectronic devices. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1995 , 13, 2570		20
201	Structural and compositional properties of the PbS-Si heterojunction. <i>Journal of Applied Physics</i> , 1980 , 51, 726-737	2.5	20
200	In-vitro evaluation of MPA-loaded electrospun coaxial fiber membranes for local treatment of glioblastoma tumor cells. <i>Journal of Drug Delivery Science and Technology</i> , 2017 , 40, 45-50	4.5	19
199	Site specific Eu ³⁺ stimulated emission in GaN host. <i>Applied Physics Letters</i> , 2006 , 88, 011111	3.4	19
198	Chapter 3 Building Blocks for SiC Devices: Ohmic Contacts, Schottky Contacts, and p-n Junctions. <i>Semiconductors and Semimetals</i> , 1998 , 52, 77-160	0.6	19
197	Fabrication of visibly photoluminescent Si microstructures by focused ion beam implantation and wet etching. <i>Applied Physics Letters</i> , 1994 , 65, 2081-2083	3.4	19
196	Photocatalytic cellulosic electrospun fibers for the degradation of potent cyanobacteria toxin microcystin-LR. <i>Journal of Materials Chemistry</i> , 2012 , 22, 12666		18
195	Stain-etched porous silicon visible light emitting diodes. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1995 , 13, 1221		18
194	Absorption of Ethylene on Membranes Containing Potassium Permanganate Loaded into Alumina-Nanoparticle-Incorporated Alumina/Carbon Nanofibers. <i>Journal of Agricultural and Food Chemistry</i> , 2018 , 66, 5635-5643	5.7	17
193	Immobilization of stable thylakoid vesicles in conductive nanofibers by electrospinning. <i>Biomacromolecules</i> , 2011 , 12, 778-84	6.9	17
192	Color tunable organic light emitting diodes using Eu complex doping. <i>Solid-State Electronics</i> , 2007 , 51, 500-504	1.7	17
191	Rare-earth-doped GaN switchable color electroluminescent devices. <i>IEEE Transactions on Electron Devices</i> , 2002 , 49, 1545-1551	2.9	17
190	Selective enhancement of blue electroluminescence from GaN:Tm. <i>Applied Physics Letters</i> , 2003 , 82, 55-574		17
189	Growth and morphology of Er-doped GaN on sapphire and hydride vapor phase epitaxy substrates. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 1195		17

188	Crystallinity and Photoluminescence in Stain-Etched Porous Si. <i>Journal of the Electrochemical Society</i> , 1994 , 141, 674-679	3.9	17
187	Growth and characterization of GaN thin films on SiC SOI substrates. <i>Journal of Electronic Materials</i> , 1997 , 26, 217-223	1.9	16
186	Liquid-state field-effect transistors using electrowetting. <i>Applied Physics Letters</i> , 2007 , 90, 043507	3.4	16
185	Versatile electrowetting arrays for smart window applications-from small to large pixels on fixed and flexible substrates. <i>Solar Energy Materials and Solar Cells</i> , 2013 , 117, 544-548	6.4	15
184	Complementary electrowetting devices on plasma-treated fluoropolymer surfaces. <i>Langmuir</i> , 2010 , 26, 9474-83	4	15
183	In Situ N ₂ -Doping of SiC Films Grown on Si(111) by Chemical Vapor Deposition from Organosilanes. <i>Journal of the Electrochemical Society</i> , 2000 , 147, 2324	3.9	15
182	. <i>IEEE Photonics Technology Letters</i> , 1993 , 5, 435-438	2.2	15
181	. <i>IEEE Electron Device Letters</i> , 1994 , 15, 507-509	4.4	15
180	Silane silicidation of Mo thin films. <i>Journal of Applied Physics</i> , 1980 , 51, 5981-5985	2.5	15
179	Self-inflating floating nanofiber membranes for controlled drug delivery. <i>International Journal of Pharmaceutics</i> , 2020 , 579, 119164	6.5	14
178	Electrical and magnetic properties of GaN codoped with Eu and Si. <i>Journal of Applied Physics</i> , 2010 , 107, 013901	2.5	14
177	Highly perfect thin films of SiC: X-ray double crystal diffractometry and X-ray double crystal topographic study. <i>Thin Solid Films</i> , 1997 , 292, 1-6	2.2	14
176	Dynamics of ultraviolet emissions in Tm-doped AlN using above band gap excitation. <i>Applied Physics Letters</i> , 2008 , 93, 061110	3.4	14
175	Excitation-Wavelength Dependent and Time-Resolved Photoluminescence Studies of Europium Doped GaN Grown by Interrupted Growth Epitaxy (IGE). <i>Materials Research Society Symposia Proceedings</i> , 2005 , 866, 1		14
174	Rare earth focused ion beam implantation utilizing Er and Pr liquid alloy ion sources. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 2791		14
173	Reduced temperature growth of crystalline 3C-SiC films on 6H-SiC by chemical vapor deposition from silacyclobutane. <i>Journal of Applied Physics</i> , 1995 , 78, 1271-1273	2.5	14
172	GaAs quantum well distributed Bragg reflection laser with AlGaAs/GaAs superlattice gratings fabricated by focused ion beam mixing. <i>Applied Physics Letters</i> , 1995 , 67, 179-181	3.4	14
171	Secondary ion mass spectrometry depth profiling of nanometer-scale p+n junctions fabricated by Ga ⁺ focused ion beam implantation. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1992 , 10, 333		14

170	Plasma etching characteristics of sputtered MoSi ₂ films. <i>Applied Physics Letters</i> , 1980 , 37, 466-468	3.4	14
169	Characterization of NbSi ₂ thin films. <i>Journal of Applied Physics</i> , 1982 , 53, 5703-5709	2.5	14
168	Photoluminescent and electroluminescent Zn/sub 2/Si/sub 0.5/Ge/sub 0.5/O/sub 4/:Mn thin films for integrated optic devices. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2002 , 8, 1420-1426	3.8	13
167	Thermal quenching of photoluminescence from Er-doped GaN thin films. <i>Journal of Alloys and Compounds</i> , 2002 , 341, 62-66	5.7	13
166	Upconversion luminescence of Er-implanted GaN films by focused-ion-beam direct write. <i>Applied Physics Letters</i> , 1999 , 75, 1833-1835	3.4	13
165	Selective compositional mixing in GaAs/AlGaAs superlattice induced by low dose Si focused ion beam implantation. <i>Journal of Applied Physics</i> , 1995 , 77, 5616-5624	2.5	13
164	Atomic probe imaging of E ₅ C thin films grown on (100) Si. <i>Applied Physics Letters</i> , 1992 , 60, 1495-1497	3.4	13
163	Edge-defined patterning of hyperfine refractory metal silicide MOS structures. <i>IEEE Transactions on Electron Devices</i> , 1981 , 28, 1364-1368	2.9	13
162	Lightweight electrowetting display on ultra-thin glass substrate. <i>Journal of the Society for Information Display</i> , 2013 , 21, 192-197	2.1	12
161	High brightness ZnS and GaN electroluminescent devices using PZT thick dielectric layers. <i>IEEE Transactions on Electron Devices</i> , 2005 , 52, 194-203	2.9	12
160	In-situ Er-doped GaN optical storage devices using high-resolution focused ion beam milling. <i>Optical Engineering</i> , 2002 , 41, 742	1.1	12
159	High-Density Er-Implanted GaN Optical Memory Devices. <i>Applied Optics</i> , 2001 , 40, 3552-8	1.7	12
158	Development of an ErNi liquid alloy ion source. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 1056		12
157	Atomic probe microscopy of 3C SiC films grown on 6H SiC substrates. <i>Applied Physics Letters</i> , 1993 , 62, 2545-2547	3.4	12
156	. <i>IEEE Transactions on Electron Devices</i> , 1980 , 27, 126-133	2.9	12
155	Chirality of sulforhodamine dye molecules incorporated in DNA thin films. <i>Applied Physics Letters</i> , 2008 , 93, 193903	3.4	11
154	Light wave coupled flat panel displays and solid-state lighting using hybrid inorganic/organic materials. <i>Journal of Display Technology</i> , 2005 , 1, 157-166		11
153	Growth and doping of SiC-thin films on low-stress, amorphous Si ₃ N ₄ /Si substrates for robust microelectromechanical systems applications. <i>Journal of Electronic Materials</i> , 2002 , 31, 361-365	1.9	11

152	Electroluminescent devices using a high-temperature stable GaN-based phosphor and thick-film dielectric layer. <i>IEEE Transactions on Electron Devices</i> , 2002 , 49, 557-563	2.9	11
151	Alternating current thin-film electroluminescence of GaN:Er. <i>Applied Physics Letters</i> , 2000 , 77, 3520-3522	3.4	11
150	Selective-area room temperature visible photoluminescence from SiC/Si heterostructures. <i>Applied Physics Letters</i> , 1994 , 64, 1419-1420	3.4	11
149	Electrochemical capacitance-voltage depth profiling of nanometer-scale layers fabricated by Ga ⁺ focused ion beam implantation into silicon. <i>Applied Physics Letters</i> , 1992 , 61, 554-556	3.4	11
148	Sub-100-nm p+n shallow junctions fabricated by group III dual ion implantation and rapid thermal annealing. <i>Applied Physics Letters</i> , 1989 , 54, 1790-1792	3.4	11
147	Ultrashallow Si p+B junction fabrication by low energy Ga ⁺ focused ion beam implantation. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1990 , 8, 1937		11
146	Charge-packet splitting in charge-domain devices. <i>IEEE Transactions on Electron Devices</i> , 1984 , 31, 1494-1501	2.9	11
145	Electrowetting on Flexible Substrates. <i>Journal of Adhesion Science and Technology</i> , 2012 , 26, 1931-1939	2	10
144	Eu-Doped GaN Films Grown by Phase Shift Epitaxy. <i>Applied Physics Express</i> , 2010 , 3, 121002	2.4	10
143	Mg 2+-doped GaN nanoparticles as blue-light emitters: a method to avoid sintering at high temperatures. <i>Small</i> , 2008 , 4, 105-110	11	10
142	Formation of SiC SOI Structures by Direct Growth on Insulating Layers. <i>Journal of the Electrochemical Society</i> , 2000 , 147, 3845	3.9	10
141	Effect of annealing temperature on 1.5 μ m photoluminescence from Er-implanted 6H-SiC. <i>Journal of Electronic Materials</i> , 1996 , 25, 869-873	1.9	10
140	Development of boron liquid metal ion source for focused ion beam system. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1987 , 5, 190		10
139	Correlation of photoluminescence and symmetry studies with photoexcitation and decay processes of infrared active defects in Si. <i>Journal of Applied Physics</i> , 1983 , 54, 4097-4103	2.5	10
138	Infrared charge coupled devices. <i>Infrared Physics</i> , 1976 , 16, 65-73		10
137	Quantitative hematocrit measurement of whole blood in a point-of-care lateral flow device using a smartphone flow tracking app. <i>Biosensors and Bioelectronics</i> , 2020 , 163, 112300	11.8	9
136	Optical and structural characterization of blue-emitting Mg ²⁺ - and Zn ²⁺ -doped GaN nanoparticles. <i>Journal of Materials Chemistry</i> , 2009 , 19, 3889		9
135	Visible lasing from GaN:Eu optical cavities on sapphire substrates. <i>Optical Materials</i> , 2006 , 28, 859-863	3.3	9

134	Extended X-ray absorption fine structure studies of GaN epilayers doped with Er. <i>Optical Materials</i> , 2006 , 28, 785-789	3.3	9
133	Low energy off-axis focused ion beam Ga ⁺ implantation into Si. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1991 , 9, 2916		9
132	Uniform SiC thin-film growth on Si by low pressure rapid thermal chemical vapor deposition. <i>Applied Physics Letters</i> , 1992 , 60, 2107-2109	3.4	9
131	Comparison of NPN transistors fabricated with broad beam and spatial profiling using focused beam ion implantation. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1986 , 4, 375		9
130	Ultralow dose effects in ion-beam induced grafting of polymethylmethacrylate (PMMA). <i>Nuclear Instruments & Methods in Physics Research B</i> , 1987 , 19-20, 1009-1012	1.2	9
129	Size effects in MoSi ₂ -gate MOSFETs. <i>Applied Physics Letters</i> , 1980 , 36, 297-299	3.4	9
128	Effect of Tm ³⁺ -induced defects on the photoexcitation energy relaxation in Tm-doped Al _x Ga _{1-x} N. <i>Physical Review B</i> , 2009 , 79,	3.3	8
127	Growth-temperature dependence of Er-doped GaN luminescent thin films. <i>Applied Physics Letters</i> , 2002 , 80, 344-346	3.4	8
126	Effect of Carbonization Gas Precursor on the Heteroepitaxial Growth of SiC-on-Si by Rtcvd. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 242, 537		8
125	Selective reactive ion etching of tungsten films in CHF ₃ and other fluorinated gases. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1988 , 6, 1073		8
124	Si p+-n shallow junction fabrication using on-axis Ga ⁺ implantation. <i>Applied Physics Letters</i> , 1988 , 52, 2049-2051	3.4	8
123	An image processing approach to fast, efficient proximity correction for electron beam lithography. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1983 , 1, 1383		8
122	Correcting the effect of hematocrit in whole blood coagulation analysis on paper-based lateral flow device. <i>Analytical Methods</i> , 2018 , 10, 2869-2874	3.2	8
121	DNA-based materials for electro-optic applications: current status 2005 , 5934, 38		7
120	New spectroscopic data of erbium ions in GaN thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2003 , 105, 126-131	3.1	7
119	GaN:Eu Interrupted Growth Epitaxy (IGE): Thin Film Growth and Electroluminescent Devices. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 866, 53		7
118	Thickness Determination of SiC - on - Si Thin Films by Anisotropic Reactive Ion Etching and Preferential Wet Etching. <i>Journal of the Electrochemical Society</i> , 1993 , 140, 178-182	3.9	7
117	Electrical properties of nanometer-scale Si p+-n junctions fabricated by low energy Ga ⁺ focused ion beam implantation. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1991 , 9, 2718		7

116	Charge-domain integrated circuits for signal processing. <i>IEEE Journal of Solid-State Circuits</i> , 1985 , 20, 562-570	5.5	7
115	Engineering a simple lateral flow device for animal blood coagulation monitoring. <i>Biomicrofluidics</i> , 2018 , 12, 014110	3.2	6
114	Deep ultraviolet photoluminescence of Tm-doped AlGaIn alloys. <i>Applied Physics Letters</i> , 2009 , 94, 111103	3.4	6
113	Effect of process conditions on gain and loss in GaN:Eu cavities on different substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 26-29	1.6	6
112	Focused ion beam fabricated microgratings for integrated optics applications. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2002 , 8, 1323-1330	3.8	6
111	Low-temperature operation of silicon surface-channel charge-coupled devices. <i>IEEE Transactions on Electron Devices</i> , 1987 , 34, 39-51	2.9	6
110	Focused Ga ⁺ beam direct implantation for Si device fabrication. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1985 , 3, 91		6
109	Particle-beam fabrication and in situ processing of integrated circuits. <i>Proceedings of the IEEE</i> , 1986 , 74, 1753-1774	14.3	6
108	The effect of annealing on the properties of silicidized molybdenum thin films. <i>Journal of Applied Physics</i> , 1981 , 52, 6331-6336	2.5	6
107	Quantitative Detection in Lateral Flow Immunoassay Using Integrated Organic Optoelectronics. <i>IEEE Sensors Journal</i> , 2017 , 17, 8343-8349	4	5
106	p-type GaN grown by phase shift epitaxy. <i>Applied Physics Letters</i> , 2014 , 104, 012108	3.4	5
105	Fabrication of natural DNA-containing organic light emitting diodes 2011 ,		5
104	Optical properties of Er in Er-doped Zn/sub 2/Si/sub 0.5/Ge/sub 0.5/O/sub 4/ waveguide amplifiers. <i>Journal of Lightwave Technology</i> , 2005 , 23, 1342-1349	4	5
103	Photoluminescence and excitation spectroscopy of the 1.5 μm Er-related band in MBE-grown GaN layers. <i>Superlattices and Microstructures</i> , 2004 , 36, 701-705	2.8	5
102	On 2.7 μm Emission from Er-doped Large Bandgap Hosts. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 866, 7		5
101	. <i>IEEE Electron Device Letters</i> , 1993 , 14, 123-125	4.4	5
100	Enhanced photoluminescence from AlGaAs/GaAs superlattice gratings fabricated by Si FIB implantation. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 281, 319		5
99	Electrical properties of Si p/sup +/-n junctions for sub-0.25 μm CMOS fabricated by Ga FIB implantation. <i>IEEE Transactions on Electron Devices</i> , 1993 , 40, 1823-1829	2.9	5

98	. <i>IEEE Electron Device Letters</i> , 1988 , 9, 594-597	4.4	5
97	Thin-layer p-n junction fabrication using Ga and In focused ion beam implantation. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1988 , 6, 977		5
96	RECIPE: A two-dimensional VLSI process modeling program. <i>IEEE Transactions on Electron Devices</i> , 1982 , 29, 216-221	2.9	5
95	Infrared optical properties of sputtered In ₂ O ₃ films. <i>Infrared Physics</i> , 1976 , 16, 145-147		5
94	Engineering DNA and Nucleobases for Present and Future Device Applications 2017 , 191-233		4
93	Latest advances in biomaterials: from deoxyribonucleic acid to nucleobases 2014 ,		4
92	Flexible electrowetting and electrowetting on flexible substrates 2011 ,		4
91	Potential for size reduction of AlGaAs optical channel waveguide structures fabricated by focused ion beam implantation and oxidation. <i>Optics Communications</i> , 1998 , 150, 97-100	2	4
90	Direct write electron beam patterning of DNA complex thin films. <i>Journal of Vacuum Science & Technology B</i> , 2008 , 26, 2567-2571		4
89	Identification of defect-trap-related europium sites in gallium nitride. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 834-837		4
88	56.3: Electrowetting Light Valves with Greater than 80% Transmission, Unlimited View Angle, and Video Response. <i>Digest of Technical Papers SID International Symposium</i> , 2005 , 36, 1674	0.5	4
87	MgGa liquid metal ion source for implantation doping of GaN. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001 , 19, 2551		4
86	CW blue-green light emission from GaN and SiC by sum-frequency generation and second harmonic generation. <i>Journal of Electronic Materials</i> , 2000 , 29, 1059-1062	1.9	4
85	CMOS-based photoreceiver arrays for page-oriented optical storage access. <i>IEEE Photonics Technology Letters</i> , 2000 , 12, 1234-1236	2.2	4
84	Optimization of solvent development in radiation induced graft lithography of poly(methylmethacrylate). <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1986 , 4, 403		4
83	Effect of substrate orientation on the properties of the Si/PbS heterojunction. <i>Solar Cells</i> , 1980 , 1, 199-208		4
82	Refractory MoSi ₂ and MoSi ₂ /polysilicon bulk CMOS Circuits. <i>IEEE Electron Device Letters</i> , 1982 , 3, 37-40	4.4	4
81	Direct injection readout of the p-n PbS-Si heterojunction detector. <i>Applied Physics Letters</i> , 1979 , 35, 537-539	3.4	4

80	and evaluation of microneedles coated with electrosprayed micro/nanoparticles for medical skin treatments. <i>Journal of Microencapsulation</i> , 2020 , 37, 517-527	3-4	4
79	Integrated NFC power source for zero on-board power in fluorescent paper-based lateral flow immunoassays. <i>Flexible and Printed Electronics</i> , 2016 , 1, 044001	3-1	4
78	Magnetic particles as liquid carriers in the microfluidic lab-in-tube approach to detect phase change. <i>ACS Applied Materials & Interfaces</i> , 2014 , 6, 8066-72	9-5	3
77	Investigation of DNA nucleobases-thin films for potential application in electronics and photonics 2013 ,		3
76	Dose effects in electron beam irradiation of DNA-complex thin films. <i>Applied Physics Letters</i> , 2010 , 97, 063702	3-4	3
75	Growth temperature dependence of optical modal gain and loss in GaN:Eu active medium on Si. <i>Optics Express</i> , 2006 , 14, 5307-12	3-3	3
74	Contrast-enhancement in black dielectric electroluminescent devices. <i>IEEE Transactions on Electron Devices</i> , 2002 , 49, 1348-1352	2-9	3
73	Effect of trimethylsilane flow rate on the growth of SiC thin-films for fiber-optic temperature sensors. <i>Journal of Microelectromechanical Systems</i> , 2003 , 12, 797-803	2-5	3
72	Transmission electron microscopy of GaN layers in-situ doped with Er during plasma assisted MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2484-2487		3
71	Excitation Power Dependence of Photoluminescence in CIB and FIB Implanted Superlattices. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 240, 697		3
70	AFM Study of Nucleation and Void Formation in SiC Carbonization of Si. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 280, 739		3
69	Enhanced plasma etch resistance of acrylic acid/calcium acetate modified poly(methylmethacrylate). <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1987 , 5, 382		3
68	Development of test bed system for high melting temperature alloy fabrication and mass spectroscopy analysis of liquid metal ion beam source. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1987 , 5, 2073-2076	2-9	3
67	Polymethyl methacrylate resist sensitivity enhancement in x-ray lithography by in situ polymerization. <i>Applied Physics Letters</i> , 1984 , 44, 973-975	3-4	3
66	Two-dimensional Haar thinning for data base compaction in Fourier proximity correction for electron beam lithography. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1985 , 3, 165		3
65	Thin Film Properties of Sputtered Niobium Silicide on SiO ₂ , Si ₃ N ₄ , and N ⁺ Poly-Si. <i>Journal of the Electrochemical Society</i> , 1986 , 133, 175-178	3-9	3
64	Auger analysis of the PbS-Si heterojunction. <i>Journal of Electronic Materials</i> , 1980 , 9, 525-549	1-9	3
63	Dynamic packet splitting in charge domain devices. <i>IEEE Electron Device Letters</i> , 1982 , 3, 268-270	4-4	3

62	CURRENT OSCILLATIONS IN CADMIUM SULPHIDE WITH OPTICALLY POLISHED PARALLEL SURFACES. <i>Applied Physics Letters</i> , 1970 , 16, 163-165	3.4	3
61	Urine-powered (galvanic) electric cell and sensor on paper substrate. <i>Flexible and Printed Electronics</i> , 2016 , 1, 044002	3.1	2
60	Direct and indirect photoluminescence excitation and ultraviolet emission from Tm-doped Al _x Ga _{1-x} N. <i>Journal of Applied Physics</i> , 2009 , 105, 083509	2.5	2
59	Stimulated emission of sulforhodamine 640 doped DNA distributed feedback (DFB) laser devices 2007 ,		2
58	Organic light emitting diode with a DNA biopolymer electron blocking layer 2006 ,		2
57	P-59: A Novel Fluorescent Display Using Light Wave Coupling Technology. <i>Digest of Technical Papers SID International Symposium</i> , 2004 , 35, 470	0.5	2
56	P-117: Electrowetting-Based Pixelation for Light Wave Coupling Displays. <i>Digest of Technical Papers SID International Symposium</i> , 2005 , 36, 746	0.5	2
55	Raman and Photoluminescence Characterization of FIB Patterned AlGaAs/GaAs Multiple Quantum Wells. <i>Materials Research Society Symposia Proceedings</i> , 1993 , 324, 193		2
54	Time Resolved Photoluminescence from Patterned GaAs/AlGaAs Multiple Quantum Well Structures. <i>Materials Research Society Symposia Proceedings</i> , 1993 , 326, 531		2
53	Measurement of complete Auger electron emission angular distributions from SiC films on Si(100). <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1994 , 12, 457-464	2.9	2
52	Characterization of optical channel waveguides formed by FIB induced compositional mixing in AlGaAs MQWs. <i>Superlattices and Microstructures</i> , 1994 , 15, 421-425	2.8	2
51	Optical Channel Waveguides in AlGaAs Multiple Quantum Well Structures Formed by Focused Ion Beam Induced Compositional Mixing. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 281, 313		2
50	Anisotropic and Selective Reactive Ion Etching of SiC in CHF ₃ and Oxygen Plasma. <i>Materials Research Society Symposia Proceedings</i> , 1986 , 76, 157		2
49	Simulation of graded-base bipolar transistor characteristics fabricated with a focused ion beam. <i>Microelectronic Engineering</i> , 1986 , 5, 179-189	2.5	2
48	Micromachining of polyimide films with focused ion beams. <i>Microelectronic Engineering</i> , 1986 , 5, 461-462.	2.5	2
47	The a.c. admittance of the p-n PbS/Si heterojunction. <i>Solid-State Electronics</i> , 1980 , 23, 715-720	1.7	2
46	Design and evaluation of ion-implanted CMOS structures. <i>IEEE Transactions on Electron Devices</i> , 1980 , 27, 578-583	2.9	2
45	Charge domain recursive filters. <i>IEEE Journal of Solid-State Circuits</i> , 1982 , 17, 597-605	5.5	2

44	Photoexcitation properties of infrared active defects induced by neutron irradiation in silicon. <i>Journal of Nuclear Materials</i> , 1982 , 108-109, 693-699	3.3	2
43	Comparison of the Optical Properties of Er ³⁺ Doped Gallium Nitride Prepared by Metalorganic Molecular Beam Epitaxy (MOMBE) and Solid Source Molecular Beam Epitaxy (SSMBE). <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 2000 , 5, 824-830		2
42	Organic Light-Emitting Diodes: Exploring the Potential of Nucleic Acid Bases in Organic Light Emitting Diodes (Adv. Mater. 46/2015). <i>Advanced Materials</i> , 2015 , 27, 7680-7680	24	1
41	Electrowetting on non-fluorinated hydrophobic surfaces. <i>Journal of the Society for Information Display</i> , 2013 , 21, 411-416	2.1	1
40	Unidirectional self-patterning of CaF ₂ nanorod arrays using capillary pressure. <i>Journal of Materials Research</i> , 2011 , 26, 223-229	2.5	1
39	I-V and Gain Characteristics of Electrowetting-Based Liquid Field Effect Transistor 2008 ,		1
38	Molecular binding and enhanced photoluminescence of bromocresol purple in marine derived DNA 2005 ,		1
37	Spectroscopic studies of the infrared emission from Tm doped Al _x Ga _{1-x} N thin films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2796-2799		1
36	Cathodoluminescence and its temperature dependence in Tm-doped Al _x Ga _{1-x} N thin films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2765-2769		1
35	AC Operation of GaN:Er Thin Film Electroluminescent Display Devices. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 639, 1041		1
34	Digital thin-film color optical memory. <i>Applied Physics Letters</i> , 2001 , 78, 255-257	3.4	1
33	The Effect of Hydrogen/ Deuterium Introduction on Photoluminescence of 3C-SiC Crystals. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 513, 445		1
32	Focused Ion Beam Micromachining of GaN Photonic Devices. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 537, 1		1
31	Visible and Infrared Rare-Earth Activated Electroluminescence From Erbium Doped GaN. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 537, 1		1
30	Focused Ion Beam Micromachining of GaN Photonic Devices. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1999 , 4, 920-925		1
29	Comparison of the Optical Properties of Er ³⁺ Doped Gallium Nitride Prepared by Metalorganic Molecular Beam Epitaxy (MOMBE) and Solid Source Molecular Beam Epitaxy (SSMBE). <i>Materials Research Society Symposia Proceedings</i> , 1999 , 595, 1		1
28	Photoluminescence of Chemically Etched Polycrystalline and Amorphous Si Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 1993 , 298, 211		1
27	. <i>IEEE Electron Device Letters</i> , 1988 , 9, 284-286	4.4	1

26	Characteristics and surface analysis of ion beam deposition from binary boron platinum (Pt58B42) liquid-metal ion source. <i>Journal of Applied Physics</i> , 1988 , 63, 878-886	2.5	1
25	Integrated PbS-Si IR detector read-out. <i>IEEE Electron Device Letters</i> , 1981 , 2, 130-132	4.4	1
24	Visible and Infrared Rare-Earth Activated Electroluminescence from Erbium Doped GaN. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1999 , 4, 940-945		1
23	Electrospinning of cyanoacrylate tissue adhesives for human dural repair in endonasal surgery. <i>Journal of Biomedical Materials Research - Part B Applied Biomaterials</i> , 2021 , 110, 660	3.5	1
22	Effect of H ₂ Additive on Reactive Ion Etching of β -SiC in CHF ₃ /O ₂ Plasma. <i>Springer Proceedings in Physics</i> , 1992 , 423-429	0.2	1
21	Fluorescence Dynamics of Er ³⁺ Ions in MBE-Grown GaN-Thin Films 2003 , 109-124		1
20	Optical and Structural Properties of Er ³⁺ -Doped GaN Grown by MBE. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1999 , 4, 435-440		1
19	Controlled drug release of parylene-coated pramipexole nanofibers for transdermal applications. <i>Surface and Coatings Technology</i> , 2021 , 409, 126831	4.4	0
18	Effect of Si and Er Co-doping on Green Electroluminescence from GaN:Er ELDs. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1068, 1		
17	Magnetic and Optical Properties of Eu-doped GaN. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 955, 1		
16	Optical and Structural Properties of Er ³⁺ -Doped GaN Grown by MBE. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 537, 1		
15	Accurate Determination of Defects in the Gate Oxide of Si Metal Oxide Semiconductor Devices by Propane Infiltration. <i>Journal of the Electrochemical Society</i> , 1993 , 140, L89-L92	3.9	
14	Characterization of Photoluminescence From Anodically Etched SiC/Si Heterostructures. <i>Materials Research Society Symposia Proceedings</i> , 1993 , 298, 361		
13	Low Energy Ion Beam Assisted Deposition of Low Resistivity Aluminum Using TMAA. <i>Materials Research Society Symposia Proceedings</i> , 1993 , 316, 863		
12	Raman Scattering Characterization of Ultrathin Films of β -SiC. <i>Materials Research Society Symposia Proceedings</i> , 1993 , 324, 267		
11	Si Nanostructure Fabrication by Ga ⁺ FIB Selective Doping and Anisotropic Etching. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 256, 123		
10	Sub-Micron Selective Photoluminescence in Porous Si by Focused Ion Beam Implantation. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 281, 519		
9	Broad and Focused Ion Beam Ga ⁺ Implantation Damage in the Fabrication of p ⁺ -n Si Shallow Junctions. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 147, 161		

- 8 Fabrication of sub-micrometer PMOSFETs with sub-100 nm p+-n shallow junctions using group III dual ion implantation. *Solid-State Electronics*, **1990**, 33, 472-474 1.7
- 7 The flip-and-shift signal enhancement application for a predictive electron-beam pattern registration model. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1986**, 4, 273
- 6 Surface analysis of palladium boride liquid metal ion beam deposition on silicon single-crystal solid surface. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1987**, 5, 1362-1366 2.9
- 5 Rapid Thermal Annealing of Fib-Implanted Ga Shallow Impurity Profiles. *Materials Research Society Symposia Proceedings*, **1987**, 101, 495
- 4 Impact of edge effects on charge-packet-splitting accuracy. *Solid-State Electronics*, **1987**, 30, 299-305 1.7
- 3 TA-A6 fundamentals and operation of charge-domain filters. *IEEE Transactions on Electron Devices*, **1980**, 27, 2184-2184 2.9
- 2 Low temperature recombination lifetime in Si metal oxide semiconductor field effect transistors. *Applied Physics Letters*, **1981**, 39, 155-156 3.4
- 1 Comparative analysis of genome code complexity and manufacturability with engineering benchmarks.. *Scientific Reports*, **2022**, 12, 2808 4.9